

自主封測 品質把控 售後保障

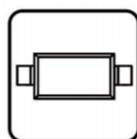
WEB | WWW.TDSEMIC.COM 



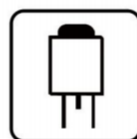
電源管理



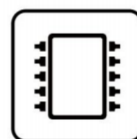
顯示驅動



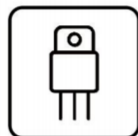
二三極管



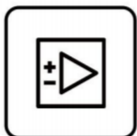
LDO穩壓器



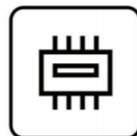
觸摸芯片



MOS管



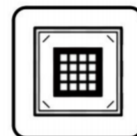
運算放大器



存儲芯片



MCU



串口通信

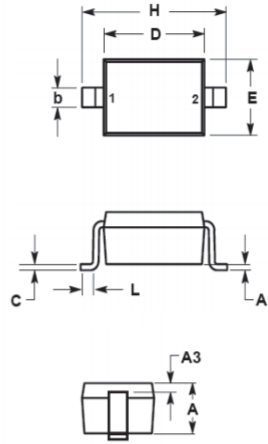
BAV21WS-TD

產品規格說明書

Features

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance

DEVICE	MARKING
BAV19WS	A8
BAV20WS	T2
BAV21WS	T3



SOD-323		
Dim.	Min.	Max.
A	0.80	1.10
A1	0.00	0.10
A3	0.15 REF	
B	0.25	0.40
C	0.10	0.15
D	1.60	1.80
E	1.15	1.35
L	0.20	0.50
H	2.30	2.80
Dimensions in millimeter		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Symbol	Parameter	Value			Unit
		BAV19WS	BAV20WS	BAV21WS	
V _{RM}	Non-Repetitive Peak Reverse Voltage	120	200	250	V
V _{RRM}	Peak Repetitive Reverse Voltage	100	150	200	V
V _{RWM}	Working Peak Reverse Voltage				
V _{R(RMS)}	RMS Reverse Voltage	71	106	141	V
I _O	Average Rectified Output Current	200			mA
I _{FSM}	Non-repetitive Peak Forward Surge Current @ t=8.3ms	2.0			A
P _D	Power Dissipation	250			mW
R _{θJA}	Thermal Resistance from Junction to Ambient	500			°C/W
T _J	Junction Temperature	150			°C
T _{stg}	Storage Temperature	-55~+150			°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Parameter	Symbol	Test conditions		Min	Typ	Max	Unit
Reverse current	I _R	V _R =100V	BAV19WS			0.1	uA
		V _R =150V	BAV20WS			0.1	
		V _R =200V	BAV21WS			0.1	
Forward voltage	V _F	I _F =100mA				1	V
		I _F =200mA				1.25	
Total capacitance	C _{tot}	V _R =0V, f=1MHz				5	pF
Reverse recovery time	t _{rr}	I _F = I _R =30mA, I _{rr} =0.1*I _R , R _L =100Ω				50	nS

TYPICAL TRANSIENT CHARACTERISTICS

